



DSS4160FDB

60V DUAL NPN LOW VCE(SAT) TRANSISTOR

Features

- BV_{CEO} > 60V
- I_C = 1A High Continuous Collector Current
- R_{CE(SAT)} = 180mΩ for a Low Equivalent On-Resistance
- Low Saturation Voltage V_{CE(SAT)} < 220mV @ 1A
- P_D up to 2.47W for Power-Demanding Applications
- R_{θJA} Efficient, 40% Lower than SOT26
- Low Profile 0.6mm High Package for Thin Applications
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)

Mechanical Data

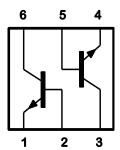
- Case: U-DFN2020-6 (Type B)
- Case Material: Molded Plastic. "Green" Molding Compound.
- UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish NiPdAu, Solderable per MIL-STD-202, Method 208
- Weight: 0.0065 grams (Approximate)

Application

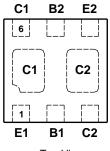
- Load Switches
- Power Management
- Charging Circuits
- Power Switches (e.g. Motors, Fans)



Bottom View



Device Symbol



Top View Pin-Out

Ordering Information (Note 4)

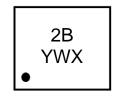
Product	Marking	Reel Size (inches)	Tape Width (mm)	Quantity per Reel
DSS4160FDB-7	2B	7	8	3,000
DSS4160FDB-7R	2B	7	8	3,000

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information

U-DFN2020-6 (Type B)



2B = Product type Marking Code

Y = Year: 0~9

W = Week: A~Z = 1~26 Week;

 $A \sim Z = 27 \sim 52 \text{ Week};$

Z Represents 52 and 53 Week

X = A~Z: Internal Code



Absolute Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	60	V
Collector-Emitter Voltage	V _{CEO}	60	V
Emitter-Base Voltage	V_{EBO}	7	V
Continuous Collector Current	I _C	1	A
Peak Pulse Collector Current	I _{CM}	1.5	A
Base Current	I _B	300	mA
Peak Base Current	I _{BM}	1	A

Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit	
	(Notes 5 & 7)		405		
Dower Dissination	(Notes 5 & 8)	0	510	mW	
Power Dissipation	(Notes 6 & 7)	P_{D}	1650		
	(Notes 6 & 8)		2470	1	
	(Notes 5 & 7)		308	°C/W	
Thermal Desistance Investigate Asshired	(Notes 5 & 8)	D	245		
Thermal Resistance, Junction to Ambient	(Notes 6 & 7)	$R_{\theta JA}$	76	· C/VV	
	(Notes 6 & 8)		51		
Thermal Resistance, Junction to Lead	(Note 9)	$R_{\theta JL}$	18	°C/W	
Operating and Storage Temperature Range		T _{J,} T _{STG}	-55 to +150	°C	

ESD Ratings (Note 10)

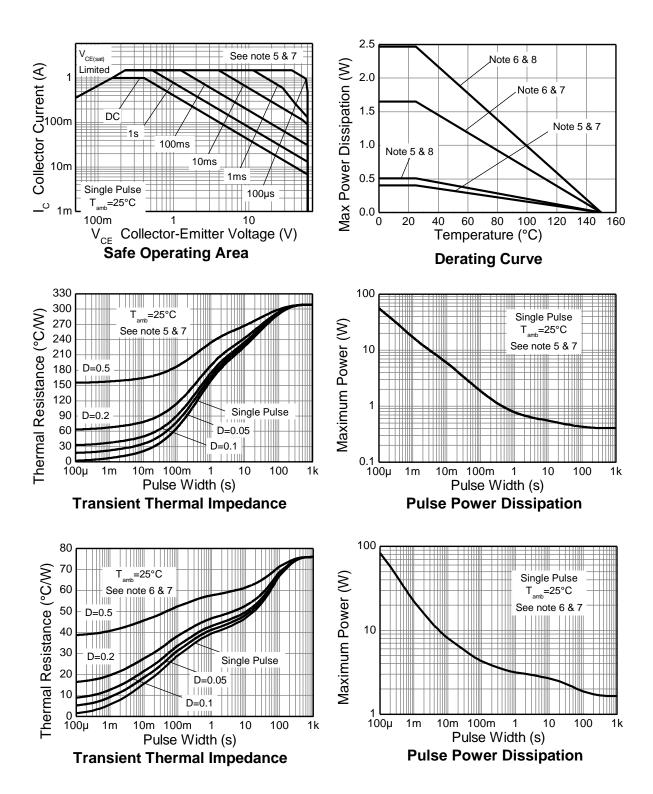
Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge – Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge – Machine Model	ESD MM	400	V	С

Notes:

- 5. For a device mounted with the exposed collector pads on minimum recommended pad layout that is on a single-sided 1.6mm FR4 PCB; device is measured under still air conditions whilst operating in a steady-state.
- 6. Same as Note (5), except the device is mounted with the collector pad on 28mm x 28mm (8cm²) 2oz copper.
- 7. For a dual device with one active die.
- 8. For dual device with 2 active die running at equal power.
- 9. Thermal resistance from junction to solder-point (on the exposed collector pads).
- 10. Refer to JEDEC specification JESD22-A114 and JESD22-A115.



Thermal Characteristics and Derating Information





Electrical Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Conditions
Collector-Base Breakdown Voltage	BV_{CBO}	60		_	V	$I_{C} = 100 \mu A$
Collector-Emitter Breakdown Voltage (Note 11)	BV_{CEO}	60	_	_	V	$I_C = 10mA$
Emitter-Base Breakdown Voltage	BV _{EBO}	7		_	V	$I_E = 100\mu A$
Collector-Base Cutoff Current	1	_		100	nA	$V_{CB} = 48V, I_{E} = 0$
	I _{CBO}	_	_	50	μΑ	$V_{CB} = 48V$, $I_E = 0$, $T_A = +150$ °C
Emitter-Base Cutoff Current	I _{EBO}	_	_	100	nA	$V_{EB} = 5.6V, I_C = 0$
		290	430	_		$V_{CE} = 2V, I_{C} = 100mA$
DC Current Gain (Note 11)	h _{FE}	150	220	_	_	$V_{CE} = 2V$, $I_C = 500mA$
		70	110	_		$V_{CE} = 2V$, $I_C = 1A$
		_	90	120		$I_C = 500 \text{mA}, I_B = 50 \text{mA}$
Collector-Emitter Saturation Voltage (Note 11)	V _{CE(SAT)}		170	220	mV	$I_C = 1A$, $I_B = 100mA$
	, ,	_	185	240		$I_C = 1A$, $I_B = 50mA$
Equivalent On-Resistance (Note 11)	R _{CE(SAT)}	_	180	240	mΩ	$I_C = 500 \text{mA}, I_B = 50 \text{mA}$
	V _{BE(SAT)}	_		1	V	$I_C = 0.5A$, $I_B = 50mA$
Base-Emitter Saturation Voltage (Note 11)		_		1.1		$I_C = 1A$, $I_B = 50mA$
		_		1.1		$I_C = 1A$, $I_B = 100mA$
Base-Emitter Turn-on Voltage (Note 11)	V _{BE(ON)}	_		0.9	V	$V_{CE} = 2V, I_{C} = 0.5A$
Transition Frequency	f_{T}	90	175	_	MHz	$V_{CE} = 10V, I_{C} = 50mA,$ f = 100MHz
Output (Collector) Capacitance	C _{OB(C)}	_	4	6	pF	$V_{CB} = -10V$, $f = 1MHz$
Turn-On Time	t _{ON}	_	105	_	ns	
Delay Time	t _D	_	15	_	ns	
Rise Time	t _R	_	90	_	ns	$V_{CC} = -10V, I_{C} = -0.5A,$
Turn-Off Time	t _{OFF}	_	540	_	ns	$I_{B1} = -I_{B2} = 25\text{mA}$
Storage Time	ts		410	_	ns]
Fall Time	t _F	_	130	_	ns	

Note:

11. Measured under pulsed conditions. Pulse width \leq 300 μ s. Duty cycle \leq 2%.



Typical Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

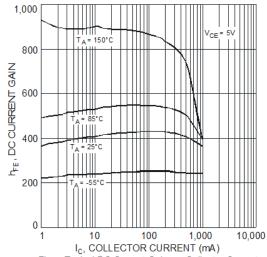


Fig. 1 Typical DC Current Gain vs. Collector Current

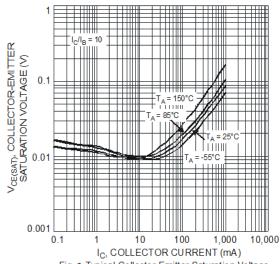
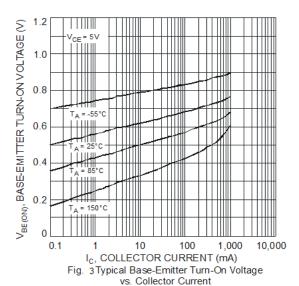
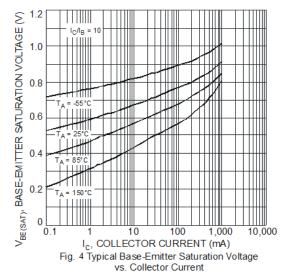


Fig. 2 Typical Collector-Emitter Saturation Voltage vs. Collector Current

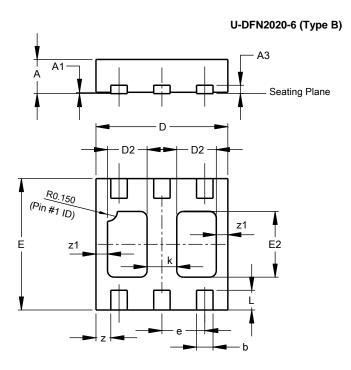






Package Outline Dimensions

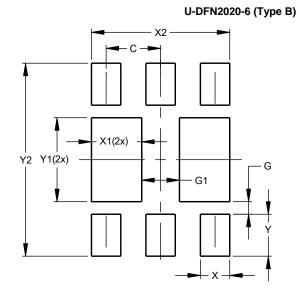
Please see http://www.diodes.com/package-outlines.html for the latest version.



U-DFN2020-6 Type B				
Dim	Min	Max	Тур	
Α	0.545	0.605	0.575	
A1	0.00	0.05	0.02	
A3	-	_	0.13	
b	0.20	0.30	0.25	
D	1.95	2.075	2.00	
D2	0.50	0.70	0.60	
е	_	_	0.65	
Е	1.95	2.075	2.00	
E2	0.90	1.10	1.00	
k	_	_	0.45	
L	0.25	0.35	0.30	
Z	-	_	0.225	
z1	_	_	0.175	
All Dimensions in mm				

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.



Dimensions	Value (in mm)		
С	0.650		
G	0.150		
G1	0.450		
Х	0.350		
X1	0.600		
X2	1.650		
Y	0.500		
Y1	1.000		
Y2	2.300		



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